Product Change Notification

Product Group: Vishay Siliconix/ May 29, 2014/**PCN-SIL-0712014 Rev 0**

Manufacturing Capacity Expansion
Low Voltage MOSFET Back-grind and Back-metallization

DESCRIPTION OF CHANGE: Vishay Siliconix announces the qualification and release to manufacturing of wafer back-grind and back-metal processes on select commercial Low Voltage MOSFET at our factory Vishay Simconix located in Shanghai, China.

Simconix is Vishay's primary Low Voltage MOSFET back-end manufacturing location. The backend assembly location controls the flow of material in its manufacturing line, and performing back-grind and back-metal processes at the assembly location improves flexibility and efficiency. This should result in a reduction in manufacturing leadtimes.

CLASSIFICATION OF CHANGE: Manufacturing capacity expansion

EXPECTED INFLUENCE ON QUALITY/RELIABILTY/PERFORMANCE: No effect on quality, reliability, and/or datasheet performance

PRODUCT CATEGORY: Commercial Low Power MOSFETs

PART NUMBERS/SERIES/FAMILIES AFFECTED:

VISHAY BRAND(s): Vishay Siliconix

TIME SCHEDULE: Phase-in for products with Simconix back-grind/back-metal processing will begin in August of 2014.

SAMPLE AVAILABILITY: Please contact your regional Vishay Sales office for sample availability.

This PCN is considered approved, without further notification, unless we receive specific customer concerns before August 29, 2014 or as specified by contract.

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PARTS LIST

Parts List
SI4156DY-T1-GE3
SI4425DDY-T1-GE3
SI4435DDY-T1-E3
SI4435DDY-T1-GE3
SI4626ADY-T1-E3
SI4686DY-T1-E3
SI4925DDY-T1-GE3
SI7106DN-T1-GE3
SI7108DN-T1-GE3
SI7234DP-T1-GE3
SI7336ADP-T1-E3
SI7336ADP-T1-GE3
SI7619DN-T1-GE3
SI7658ADP-T1-GE3
SI7686DP-T1-E3
SI7880ADP-T1-E3
SIR158DP-T1-GE3
SIR164DP-T1-GE3
SIR470DP-T1-GE3
SIR800DP-T1-GE3
SIR850DP-T1-GE3-S
SIS402DN-T1-GE3
SIS407DN-T1-GE3
V30329-T1-E3
V30397-T1-GE3

Qualification Results for Vishay Simconix Back-grind and Back-metal Manufacturing

Qualification test	Conditions	# of Lots, # of samples per lot	Time Scale Hours/Cycles	Results: samples tested/# of failures	Comments
Solder Reflow Preconditioning	24 hr 125°C Bake, 168 hr 85/85, 3 cyc @ 260C max				Prior to Test 3 & 5
1. HTGB	Ta = 150°C Vgs = 100% rating of Vgs	3 Lots, 82 samples per lot	168 Hours 500 hours	246/0	
2. HTRB	Ta = 150°C Vds = 80% rating of Vds	3 Lots, 82 samples per lot	168 Hours 500 hours	246/0	
3. Temperature Cycling	-65°C to +150°C	3 Lots, 55 samples per lot	250 Cycles 500 Cycles 1000 Cycles	165/0	
4. Pressure Pot	+121°C, 15 PSIG	3 Lots, 55 samples per lot	96 Hours	165/0	
5. HAST	+130°C, 85%RH Vgs = 100% rating	3 Lots, 55 samples per lot	100 Hours	110/0	
6. Die Saw	Check Backmetal Peeling	10 sample	N/A	100/0	Visual Inspection
7. Die Shear	MIL-STD-750	100 samples at wafer edge	N/A	100/0	Visual Inspection